

SE4942B

**N-Channel Enhancement-Mode MOSFET**

Revision: A

**General Description**

Thigh Density Cell Design For Ultra Low On-Resistance Fully Characterized Avalanche Voltage and Current Improved Shoot-Through FOM

- Simple Drive Requirement
- Small Package Outline
- Surface Mount Device

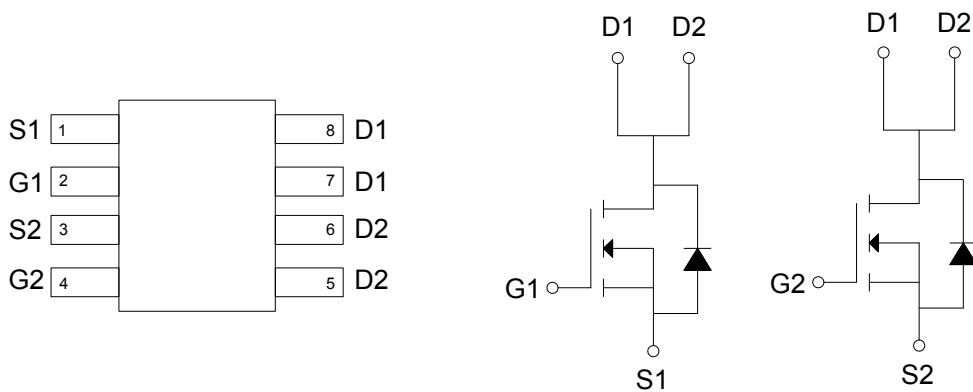
**Features**

For a single MOSFET

- $V_{DS} = 40V$
- $R_{DS(ON)} = 7m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} = 16m\Omega @ V_{GS}=4.5V$

**Pin configurations**

See Diagram below



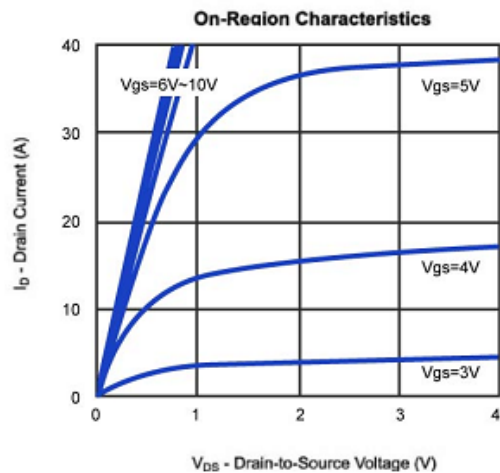
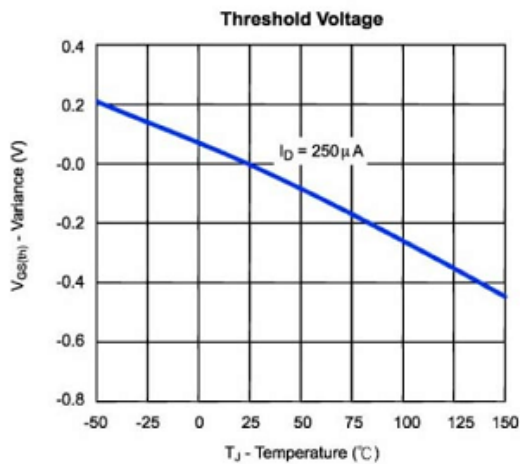
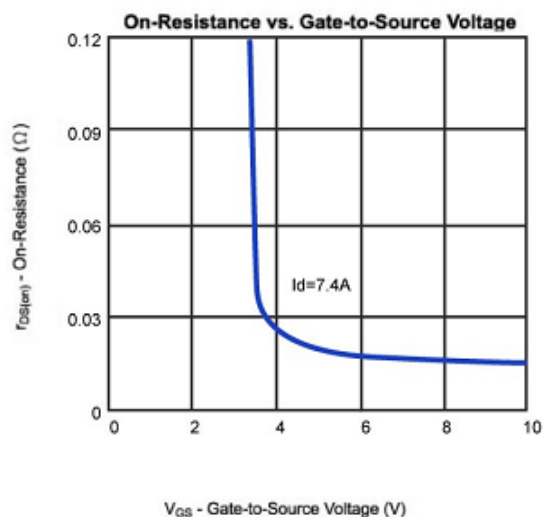
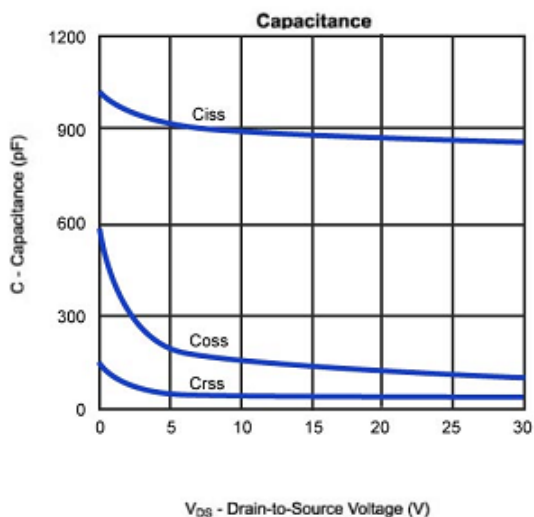
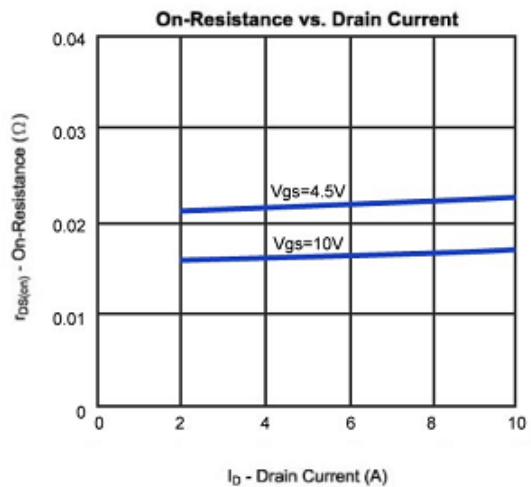
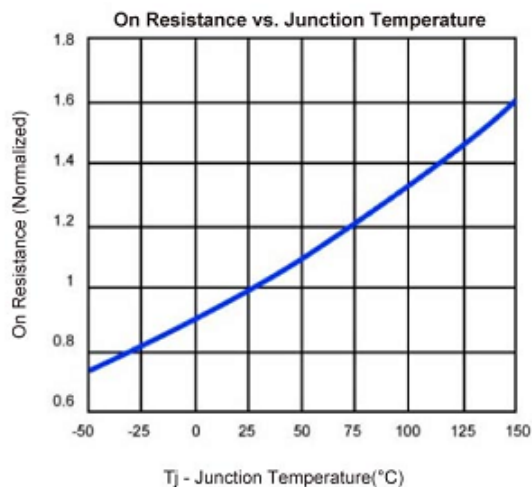
**Absolute Maximum Ratings**

Parameter		Symbol	Rating	Units
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	Continuous	$I_D$	12	A
	Pulsed		32	
Total Power Dissipation	@TA=25°C	$P_D$	2	W
Operating Junction Temperature Range		$T_J$	-55 to 150	°C

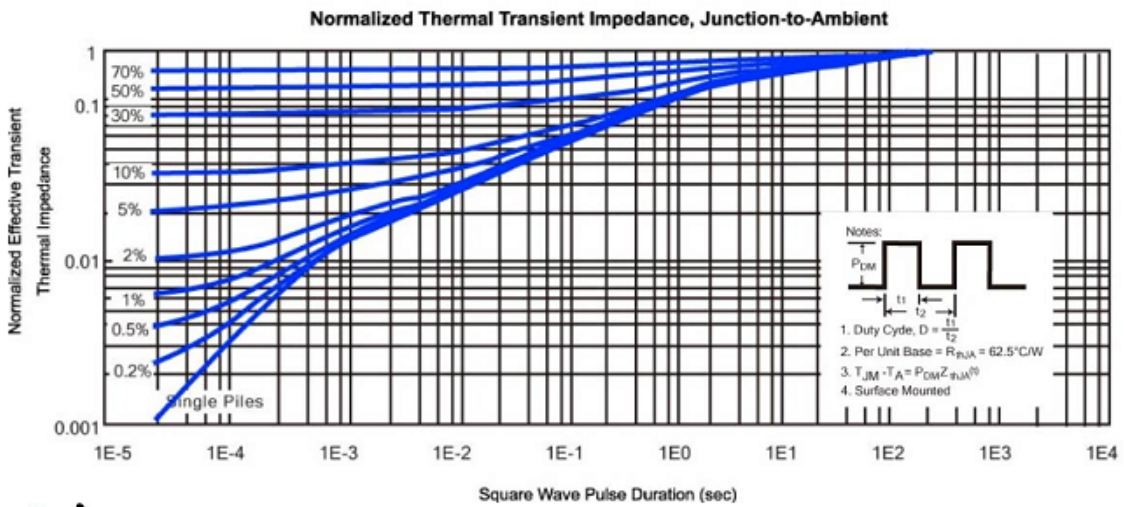
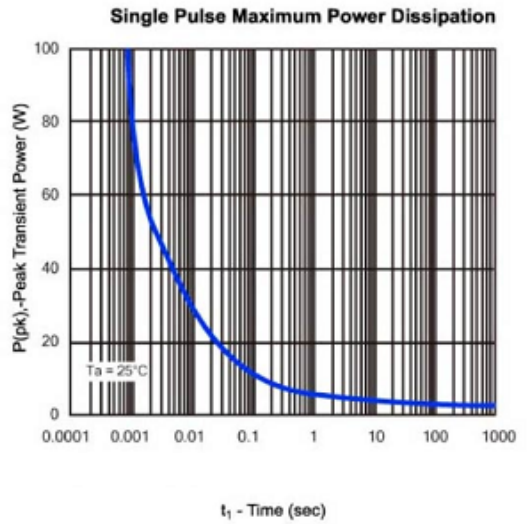
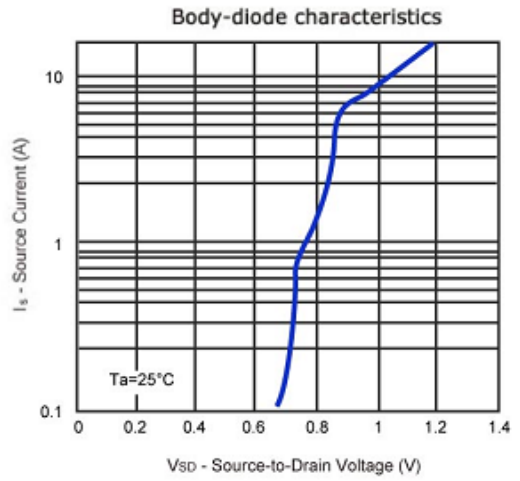
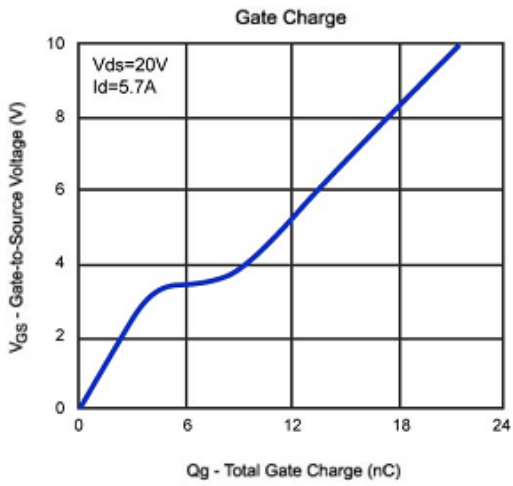
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Electrical Characteristics (T <sub>J</sub> =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS (Note 2)</b>						
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0 V	40			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>DS</sub> = 40V, V <sub>GS</sub> =0V			1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =20 V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.5		3.0	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =7.4A	-	7	13	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.4A		16	22	mΩ
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1.8A		0.8	1.2	V
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		884		pF
C <sub>oss</sub>	Output Capacitance			124		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			39		pF
<b>SWITCHING PARAMETERS</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =20V, R <sub>L</sub> =20Ω R <sub>GEN</sub> =10Ω R <sub>G</sub> =6Ω		15		ns
t <sub>d(off)</sub>	Turn-Off Delay Time			45		ns
t <sub>d(r)</sub>	Turn-On Rise Time			11		ns
t <sub>d(f)</sub>	Turn-Off Fall Time			6		ns
<b>Thermal Resistance</b>						
Symbol	Parameter		Typ	Max	Units	
R <sub>θJA</sub>	Junction to Ambient (each bin with recommended lands)		-	62.5	°C/W	

Typical Characteristics



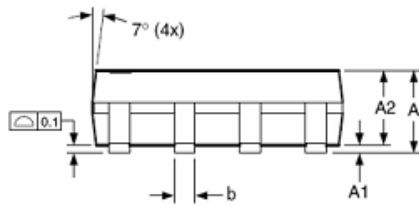
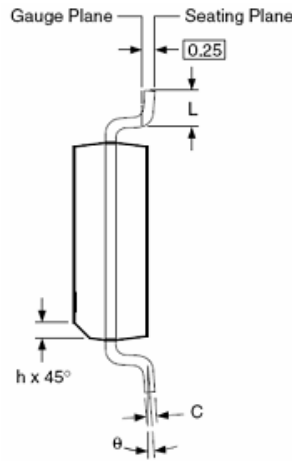
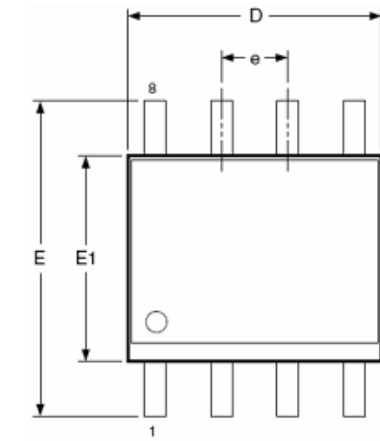
Typical Characteristics



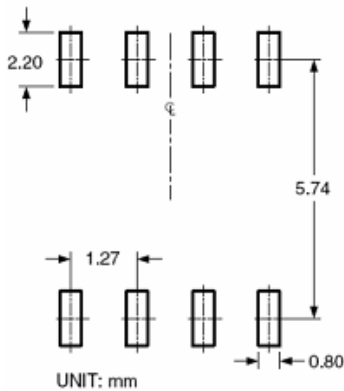
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## Package Outline Dimension

### SOP-8



#### RECOMMENDED LAND PATTERN



#### Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	1.35	1.65	1.75
A1	0.10	—	0.25
A2	1.25	1.50	1.65
b	0.31	—	0.51
c	0.17	—	0.25
D	4.80	4.90	5.00
E1	3.80	3.90	4.00
e	1.27 BSC		
E	5.80	6.00	6.20
h	0.25	—	0.50
L	0.40	—	1.27
θ	0°	—	8°

#### Dimensions in inches

Symbols	Min.	Nom.	Max.
A	0.053	0.065	0.069
A1	0.004	—	0.010
A2	0.049	0.059	0.065
b	0.012	—	0.020
c	0.007	—	0.010
D	0.189	0.193	0.197
E1	0.150	0.154	0.157
e	0.050 BSC		
E	0.228	0.236	0.244
h	0.010	—	0.020
L	0.016	—	0.050
θ	0°	—	8°

#### NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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SHANGHAI SINO-IC MICROELECTRONICS CO., LTD

Add: Building 3, Room 3401-03, No.200 Zhangheng Road,  
ZhangJiang Hi-Tech Park, Pudong, Shanghai 201203, China

Phone: +86-21-33932402 33932403

33932405 33933508 33933608

Fax: +86-21-33932401

Email: [webmaster@sino-ic.com](mailto:webmaster@sino-ic.com)

Website: <http://www.sino-ic.com>